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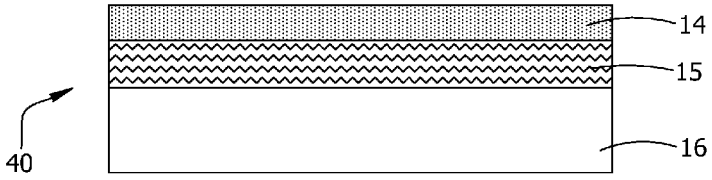
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(54) Title: METHOD FOR MONITORING THE AMOUNT OF CONTAMINATION IMPARTED INTO SEMICONDUCTOR WAFERS DURING WAFER PROCESSING

FIG. 1



(57) Abstract: Methods are disclosed for monitoring the amount of metal contamination imparted during wafer processing operations such as polishing and cleaning. The methods include subjecting a silicon-on-insulator structure to the semiconductor process, precipitating metal contamination in the structure and delineating the metal contaminants.

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